

2SD1007 (NPN)

Features

● High collector to emitter voltage: VcEo>120V.

Absolute Maximum Ratings Ta = 25° C

Parameter	Symbol	Rating	Unit
Collector-base voltage	Vсво	120	V
Collector-emitter voltage	VCEO	120	V
Emitter-base voltage	VEBO	5	V
Collector current	Ic	0.7	Α
Collector current (pulse) *	IC (pu)	1.2	Α
Collector power dissipation	Pc	2	W
Junction temperature	Tj	150	$^{\circ}$
Storage temperature	Tstg	-55 to +150	$^{\circ}$ C



1. BASE 2. COLLECTO SOT-89 3. EMITTER

Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Тур	Max	Unit
Base-emitter voltage *	VBE	VcE =10V , Ic = 10mA	550	620	650	mV
Collector cutoff current	Ісво	Vcb = 120V, IE=0			100	nA
Emitter cutoff current	ІЕВО	VEB = 5V, IC=0			100	nA
DC current gain *	hFE	VcE =1V , Ic = 5.0mA	45	200		
		VcE =1V , Ic = 100mA	90	200	400	
Collector-emitter saturation voltage *	VCE(sat)	Ic = 500mA , Iв = 50mA		0.3	0.6	V
Base-emitter saturation voltage *	VBE(sat)	Ic = 500mA , Iв = 50mA		0.9	1.5	V
Output capacitance	Cob	Vсв = 10V , IE = 0 , f = 1.0МHz		10		pF
Transition frequency	f⊤	Vce = 10V , Ie = -10mA		90		MHz

^{*.} PW≤350µs,duty cycle≤2%

hFE Classification

Marking	HR	HQ	HP
hFE	90~180	135~270	200~400

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Bipolar Transistors - BJT category:

Click to view products by Hottech manufacturer:

Other Similar products are found below:

619691C MCH4017-TL-H MJ15024/WS MJ15025/WS BC546/116 BC556/FSC BC557/116 BSW67A HN7G01FU-A(T5L,F,T NJVMJD148T4G NSVMMBT6520LT1G NTE187A NTE195A NTE2302 NTE2302 NTE2330 NTE2353 NTE316 IMX9T110 NTE63 NTE65 C4460 SBC846BLT3G 2SA1419T-TD-H 2SA1721-O(TE85L,F) 2SA1727TLP 2SA2126-E 2SB1202T-TL-E 2SB1204S-TL-E 2SC5488A-TL-H 2SD2150T100R SP000011176 FMC5AT148 2N2369ADCSM 2SB1202S-TL-E 2SC2412KT146S 2SC4618TLN 2SC5490A-TL-H 2SD1816S-TL-E 2SD1816T-TL-E CMXT2207 TR CPH6501-TL-E MCH4021-TL-E BC557B TTC012(Q) BULD128DT4 JANTX2N3810 Jantx2N5416 US6T6TR KSF350 068071B